

# RF MOS FIELD EFFECT TRANSISTOR

## DESCRIPTION:

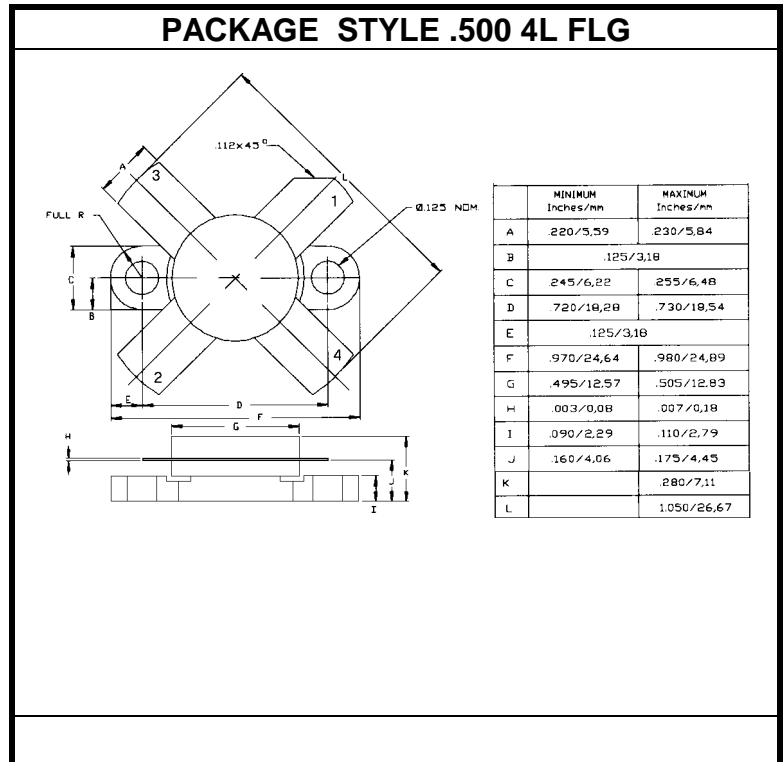
The **SRF4245** is Designed for class AB HF/VHF Applications up to 200 MHz

## FEATURES:

- $P_G = 8$  dB at 150 MHz
- **Omnigold™** Metallization System

## MAXIMUM RATINGS

$I_D$	13.9 A
$V_{(BR)DS}$	125 V
$V_{DGR}$	125 V
$V_{GS}$	$\pm 30$ V
$P_{DISS}$	215 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$\theta_{JC}$	0.70 (Typ) $^\circ C/W$



## CHARACTERISTICS $T_C = 25^\circ C$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	$V_{GS} = 0$ V	$I_D = 100$ mA		125			V
$I_{DSS}$	$V_{DS} = 50$ V	$V_{GS} = 0$ V				5	mA
$I_{GSS}$	$V_{GS} = 20$ V	$V_{DS} = 0$ V				1	$\mu A$
$V_{FEDS(on)}$	$V_{GS} = 10$ V	$I_D = 10$ A				5	V
$G_{FS}$	$V_{DS} = 10$ V	$I_D = 5.0$ A		4			mhos
$C_{ISS}$	$V_{DS} = 50$ V	$V_{GS} = 0$ V	F = 1.0 MHz			500	pF
$C_{OSS}$						250	
$C_{RSS}$						50	
$P_{OUT}$	$V_{DS} = 50$ V	$I_{DQ} = 250$ mA	F = 150 MHz	150			W
$P_G$				8			dB

